ABSTRACT OF THE DISCLOSURE

Provided is a III-V compound semiconductor having a layer formed from a first III-V compound semiconductor expressed by the general formula $In_uGa_vAl_wN$ (where $0 \leqq u \leqq 1$, $0 \leqq v \leqq 1$, $0 \leqq w \leqq 1$, $u + v + w = 1$), a pattern formed on the layer from a material different not only from the first III-V compound semiconductor but also from a second III-V compound semiconductor hereinafter described, and a layer formed on the first III-V compound semiconductor and the pattern from the second III-V compound semiconductor expressed by the general formula $In_xGa_yAl_zN$ (where $0 \leqq x \leqq 1$, $0 \leqq y \leqq 1$, $0 \leqq z \leqq 1$, $x + y + z = 1$), wherein the full width at half maximum of the (0004) reflection X-ray rocking curve of the second III-V compound semiconductor is 700 seconds or less regardless of the direction of X-ray incidence. In the III-V compound semiconductor, which is a high quality semiconductor, the occurrence of low angle grain boundaries is suppressed.